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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: *Kie Y. Ahn et al.*

Title: *MAR 14 2005 LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRIC LAYERS*

ocket No.: *1303.101US1*

Serial No.: *10/602,323*

Filed: *JUNE 24, 2003*

Due Date: *N/A*

Examiner: *Fernando L Toledo*

Group Art Unit: *2823*

MS Amendment

Commissioner for Patents

P.O. Box 1450
Alexandria, VA 22313-1450

We are transmitting herewith the following attached items (as indicated with an "X"):

A return postcard.
 A Communication Concerning Related Applications (3 pgs.).
 A Supplemental Information Disclosure Statement (2 pgs.), Form 1449 (5 pgs.), and copies of 12 cited documents.

If not provided for in a separate paper filed herewith, Please consider this a PETITION FOR EXTENSION OF TIME for sufficient number of months to enter these papers and please charge any additional fees or credit overpayment to Deposit Account No. 19-0743.

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.

Customer Number 21186

By: *David R. Cochran*
Atty: *David R. Cochran*
Reg. No. 46,632

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: MS Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 9 day of March, 2005.

Name KACIA LEE

Signature Kacia Lee

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.

(GENERAL)



STN 10/602,323

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Kie Y. Ahn et al. Examiner: Fernando L. Toledo
Serial No.: 10/602,323 Group Art Unit: 2823
Filed: June 24, 2003 Docket: 1303.101US1
Title: LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRIC LAYERS

COMMUNICATION CONCERNING RELATED APPLICATION(S)

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Applicants would like to bring to the Examiner's attention the following related application(s) in the above-identified patent application:

<u>Serial/Patent No.</u>	<u>Filing Date</u>	<u>Attorney Docket</u>	<u>Title</u>
11/036296	January 14, 2005	1303.030US2	LOW-TEMPERATURE GROWN HIGH QUALITY ULTRA-THIN CoTiO ₃ GATE DIELECTRICS
10/909959	August 2, 2004	1303.114US1	ATOMIC LAYER DEPOSITION OF ZIRCONIUM-DOPED TANTALUM OXIDE FILMS
10/931533	August 31, 2004	1303.119US1	ATOMIC LAYER DEPOSITED TITANIUM ALUMINUM OXIDE FILMS
10/926812	August 26, 2004	1303.121US1	RUTHENIUM GATE FOR A LANTHANIDE OXIDE DIELECTRIC LAYER
10/930167	August 31, 2004	1303.122US1	ATOMIC LAYER DEPOSITED LANTHANUM ALUMINUM OXIDE DIELECTRIC LAYER
10/929272	August 30, 2004	303.802US2	ATOMIC LAYER DEPOSITION AND CONVERSION
10/930138	August 31, 2004	1303.044US2	EVAPORATION OF Y-Si-O FILMS FOR MEDIUM-k DIELECTRICS
10/930184	August 31, 2004	1303.021US2	CRYSTALLINE OR AMORPHOUS MEDIUM-k GATE OXIDES, Y ₂ O ₃ AND GD ₂ O ₃

10/930516	August 31, 2004	1303.078US2	ATOMIC LAYER DEPOSITED HfSiON DIELECTRIC FILMS
10/931341	August 31, 2004	1303.082US2	ATOMIC LAYER DEPOSITED ZR-SN-TI-O FILMS USING TiI4
10/930431	August 31, 2004	1303.056US2	ATOMIC LAYER-DEPOSITED HfAlO3 FILMS FOR GATE DIELECTRICS
10/931365	August 31, 2004	1303.059US2	Pr2O3-BASED La-oxide GATE DIELECTRICS
10/931364	August 31, 2004	1303.069US2	LANTHANIDE DOPED TiOx DIELECTRIC FILMS BY PLASMA OXIDATION
10/931343	August 31, 2004	1303.101US2	LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRIC LAYERS
10/931340	August 31, 2004	1303.107US2	LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRICS
10/931845	August 31, 2004	303.717US2	METHODS, SYSTEMS, AND APPARATUS FOR UNIFORM CHEMICAL-VAPOR DEPOSITIONS
10/931595	August 31, 2004	303.717US3	METHODS, SYSTEMS, AND APPARATUS FOR UNIFORM CHEMICAL-VAPOR DEPOSITIONS
10/931356	August 31, 2004	1303.026US2	HIGHLY RELIABLE AMORPHOUS HIGH-K GATE OXIDE ZrO2
11/010529	December 13, 2004	1303.126US1	ATOMIC LAYER DEPOSITED LANTHANUM HAFNIUM OXIDE DIELECTRICS
11/029757	January 5, 2005	1303.127US1	ATOMIC LAYER DEPOSITED HAFNIUM TANTALUM OXIDE DIELECTRICS
11/010766	December 13, 2004	1303.129US1	HYBRID ALD-CVD OF PrXOY/ZrO2 FILMS AS GATE DIELECTRICS

11/053577	February 8, 2005	1303.131US1	ATOMIC LAYER DEPOSITION OF DY-DOPED HFO ₂ FILMS AS GATE DIELECTRICS
11/058563	February 15, 2005	1303.133US1	ATOMIC LAYER DEPOSITION OF Zr ₃ N ₄ /ZrO ₂ FILMS AS GATE DIELECTRICS
	February 23, 2005	1303.134US1	ATOMIC LAYER DEPOSITION OF Hf ₃ N ₄ /HfO ₂ FILMS AS GATE DIELECTRICS
11/031289	January 7, 2005	1303.069US3	LANTHANIDE DOPED TiO _x DIELECTRIC FILMS BY PLASMA OXIDATION
11/059594	February 16, 2005	1303.046US2	EVAPORATED LaAlO ₃ FILMS FOR GATE DIELECTRICS

Respectfully submitted,

KIE Y. AHN ET AL.

By Applicants' Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
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Date 9 March 2005

By


David R. Cochran
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KACIA LEE
Name

Kacia Lee
Signature



S/N 10/602,323

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Kie Y. Ahn et al. Examiner: Fernando L Toledo
Serial No.: 10/602,323 Group Art Unit: 2823
Filed: June 24, 2003 Docket: 1303.101US1
Title: LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRIC LAYERS

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

MS Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Supplemental Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. §1.97(b), it is believed that no fee or statement is required with the Supplemental Information Disclosure Statement. However, if an Office Action on the merits has been mailed, the Commissioner is hereby authorized to charge the required fees to Deposit Account No. 19-0743 in order to have this Supplemental Information Disclosure Statement considered.

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Pursuant to 37 C.F.R. 1.98(a)(2), Applicant believes that copies of cited U.S. Patents and Published Applications are no longer required to be provided to the Office. Notification of this change was provided in the United States Patent and Trademark Office OG Notices dated October 12, 2004. Thus, Applicant has not included copies of any US Patents or Published Applications cited with this submission. Should the Office require copies to be provided, Applicant respectfully requests that notice of such requirement be directed to Applicant's below-signed representative. Applicant acknowledges the requirement to submit copies of foreign patent documents and non-patent literature in accordance with 37 C.F.R. 1.98(a)(2).

Respectfully submitted,

KIE Y. AHN ET AL.

By their Representatives,

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Date 9 March 2005

By David R. Cochran
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Reg. No. 46,632

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Name KACIA LEE

Signature Kacia Lee

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <small>(Use as many sheets as necessary)</small>		Complete if Known	
		Application Number	10/602,323
		Filing Date	June 24, 2003
		First Named Inventor	Ahn, Kie
		Group Art Unit	2823
		Examiner Name	Toledo, Fernando
Sheet 1 of 5		Attorney Docket No: 1303.101US1	

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EXAMINER

DATE CONSIDERED

Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
(Use as many sheets as necessary)

Complete if Known

Application Number	10/602,323
Filing Date	June 24, 2003
First Named Inventor	Ahn, Kie
Group Art Unit	2823
Examiner Name	Toledo, Fernando

Sheet 2 of 5

Attorney Docket No: 1303.101US1

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EXAMINER

DATE CONSIDERED

Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
(Use as many sheets as necessary)

Complete if Known

Application Number	10/602,323
Filing Date	June 24, 2003
First Named Inventor	Ahn, Kie
Group Art Unit	2823
Examiner Name	Toledo, Fernando

Sheet 3 of 5

Attorney Docket No: 1303.101US1

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EXAMINER

DATE CONSIDERED

Substitute for form 1449A/PTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>		Application Number	10/602,323
		Filing Date	June 24, 2003
		First Named Inventor	Ahn, Kie
		Group Art Unit	2823
		Examiner Name	Toledo, Fernando
Sheet 4 of 5		Attorney Docket No: 1303.101US1	

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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		CHIN, A. , et al., "High Quality La ₂ O ₃ and Al ₂ O ₃ Gate Dielectrics with Equivalent Oxide Thickness 5-10A", <u>Digest of Technical Papers. 2000 Symposium on VLSI Technology, 2000</u> , Honolulu,(June 13-15, 2000),16-17	
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>		<i>Complete if Known</i>	
		Application Number	10/602,323
		Filing Date	June 24, 2003
		First Named Inventor	Ahn, Kie
		Group Art Unit	2823
		Examiner Name	Toledo, Fernando
Sheet 5 of 5		Attorney Docket No: 1303.101US1	

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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